

RJK0328DPB

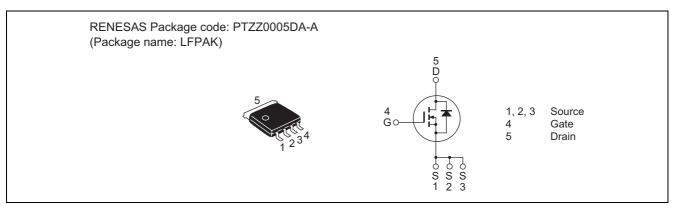
Silicon N Channel Power MOS FET Power Switching

> REJ03G1637-0400 Rev.4.00 Apr 10, 2008

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 - $R_{DS(on)} = 1.6 \text{ m}\Omega \text{ typ.} (at V_{GS} = 10 \text{ V})$
- Pb-free

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	60	A
Drain peak current	Note1 I _{D(pulse)}	240	A
Body-drain diode reverse drain current	I _{DR}	60	A
Avalanche current	I _{AP} Note 2	30	A
Avalanche energy	E _{AR} Note 2	90	mJ
Channel dissipation	Pch Note3	65	W
Channel to Case Thermal Resistance	θch-C	1.93	°C/W
Channel temperature	Tch	150	٥C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \leq 10 \ \mu s, \ duty \ cycle \leq 1\%$

2. Value at Tch = 25°C, Rg \geq 50 Ω

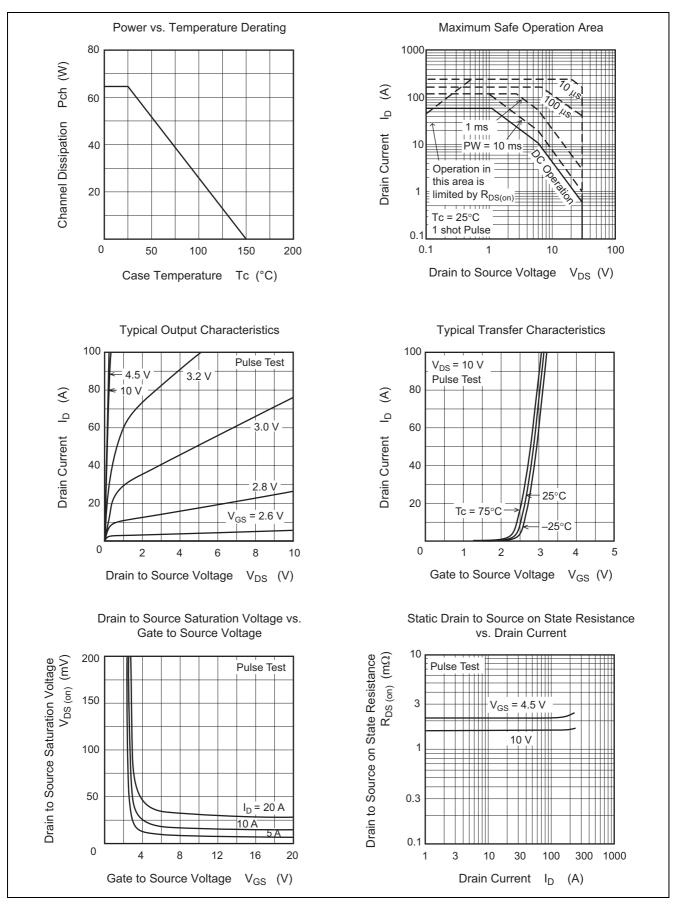
3. Tc = 25°C

Electrical Characteristics

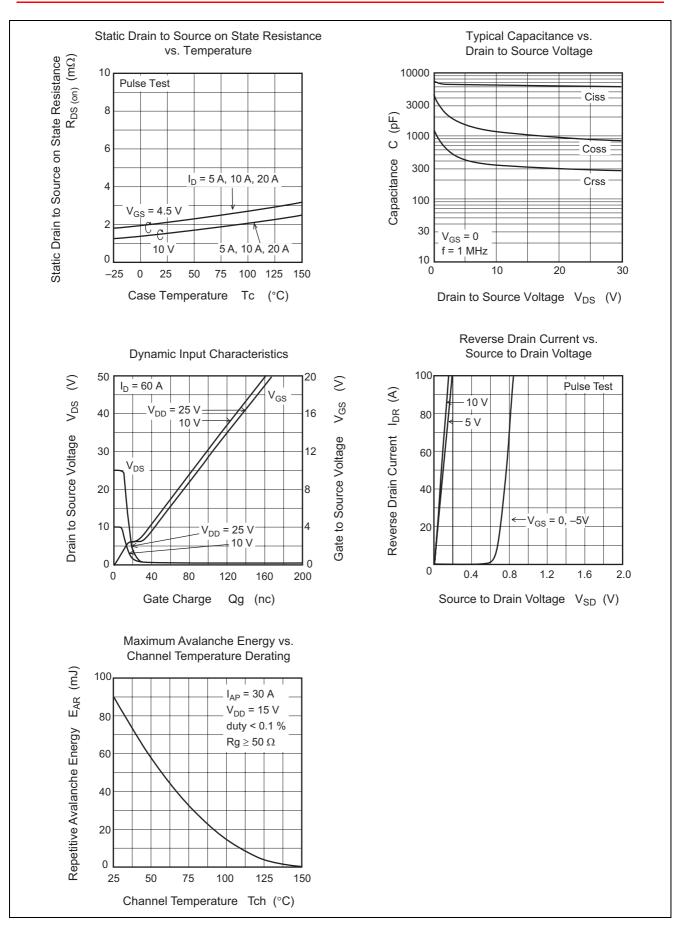
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±0.1	μΑ	$V_{GS}=\pm 20~V,~V_{DS}=0$
Zero gate voltage drain current	I _{DSS}	—	—	1	μΑ	$V_{DS} = 30 V, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.2	—	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	—	1.6	2.1	mΩ	$I_D = 30 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R _{DS(on)}	—	2.1	2.9	mΩ	$I_D = 30 \text{ A}, V_{GS} = 4.5 \text{ V}^{Note4}$
Forward transfer admittance	y _{fs}	—	100		s	$I_D = 30 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	—	6380		рF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$ f = 1 MHz
Output capacitance	Coss	—	1150		рF	
Reverse transfer capacitance	Crss	—	330		pF	
Gate Resistance	Rg	_	0.7	—	Ω	
Total gate charge	Qg	_	42	—	nC	$V_{DD} = 10 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$ $I_D = 60 \text{ A}$
Gate to source charge	Qgs	_	15	—	nC	
Gate to drain charge	Qgd	—	8.8		nC	
Turn-on delay time	t _{d(on)}	—	9.4		ns	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A},$
Rise time	tr	—	4.3		ns	$\label{eq:VDD} \begin{split} V_{\text{DD}} &\cong 10 \text{ V}, \text{R}_{\text{L}} = 0.33 \Omega, \\ \text{Rg} &= 4.7 \Omega \end{split}$
Turn-off delay time	t _{d(off)}	—	61.5		ns	
Fall time	t _f	_	7.3	—	ns	
Body-drain diode forward voltage	V _{DF}	—	0.78	1.02	V	$I_F = 60 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery	t _{rr}	—	42		ns	$I_F = 60 \text{ A}, V_{GS} = 0$
time						di _F / dt = 100 A/ μs
Body-drain diode reverse recovery	Qrr	—	46	—	nC	
charge						

Notes: 4. Pulse test

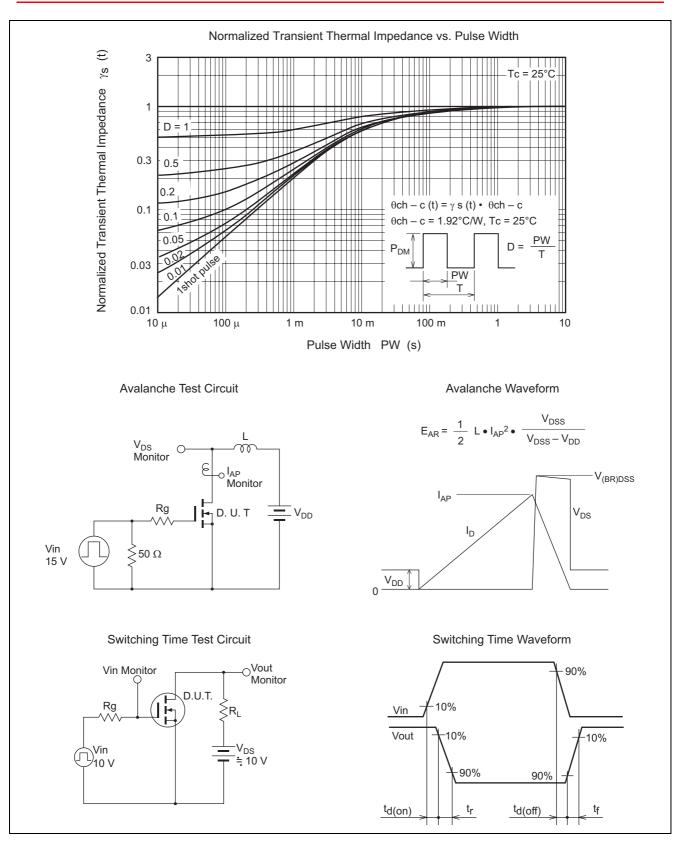
Main Characteristics



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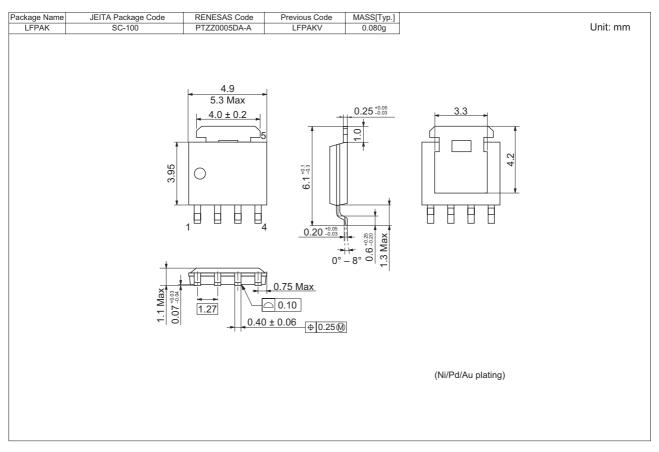


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0328DPB-00-J0	2500 pcs	Taping

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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